



## N-Channel NexFET™ Power MOSFET

Check for Samples: CSD16322Q5

#### **FEATURES**

- · Optimized for 5V Gate Drive
- Ultralow Q<sub>q</sub> and Q<sub>qd</sub>
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5-mm × 6-mm Plastic Package

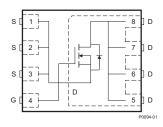
#### **APPLICATIONS**

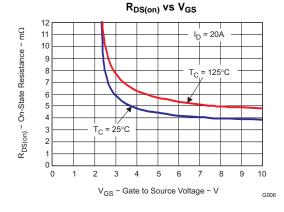
- Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems
- Synchronous or Control FET Applications

#### DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications.







#### PRODUCT SUMMARY

$V_{DS}$	Drain to Source Voltage	25	٧	
$Q_g$	Gate Charge Total (4.5V) 6.8		6.8	
$Q_{gd}$	Sate Charge Gate to Drain 1.3			nC
		$V_{GS} = 3V$	5.4	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = 4.5V$	4.6	mΩ
		$V_{GS} = 8V$	3.9	mΩ
V <sub>GS(th)</sub>	Threshold Voltage	1.1		V

#### ORDERING INFORMATION

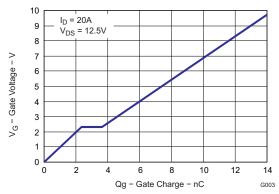
Device	Package	Media	Qty	Ship
CSD16322Q5	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

#### **ABSOLUTE MAXIMUM RATINGS**

T <sub>A</sub> = 2	5°C unless otherwise stated	VALUE	UNIT
$V_{DS}$	Drain to Source Voltage	25	٧
$V_{GS}$	Gate to Source Voltage	+10 / -8	<b>V</b>
	Continuous Drain Current, T <sub>C</sub> = 25°C	97	Α
I <sub>D</sub>	Continuous Drain Current <sup>(1)</sup>	21	Α
$I_{DM}$	Pulsed Drain Current, T <sub>A</sub> = 25°C <sup>(2)</sup>	136	Α
$P_D$	Power Dissipation <sup>(1)</sup>	3.1	W
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C
E <sub>AS</sub>	Avalanche Energy, single pulse $I_D$ = 50A, L = 0.1mH, $R_G$ = 25 $\Omega$	125	mJ

- (1) Typical  $R_{\theta JA}=39^{\circ} C/W$  on 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.
- (2) Pulse duration ≤300µs, duty cycle ≤2%





Instruments semiconductor products

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## **ELECTRICAL CHARACTERISTICS**

(T<sub>A</sub> = 25°C unless otherwise stated)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Cl	naracteristics					
BV <sub>DSS</sub>	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25			V
I <sub>DSS</sub>	Drain to Source Leakage Current	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 20V			1	μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +10/-8V$			100	nA
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.9	1.1	1.4	V
		$V_{GS} = 3V$ , $I_D = 20A$		5.4	7.2	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 20A$		4.6	5.8	mΩ
		$V_{GS} = 8V, I_{D} = 20A$		3.9	5	mΩ
9 <sub>fs</sub>	Transconductance	$V_{DS} = 15V, I_D = 20A$		106		S
Dynamic	: Characteristics	•	,		•	
C <sub>iss</sub>	Input Capacitance			1050	1365	pF
C <sub>oss</sub>	Output Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V,$ $f = 1MHz$		740	950	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 10012		55	70	pF
R <sub>G</sub>	Series Gate Resistance			1.1	2.2	Ω
Qg	Gate Charge Total (4.5V)			6.8	9.7	nC
Q <sub>gd</sub>	Gate Charge Gate to Drain	V <sub>DS</sub> = 12.5V,		1.3		nC
Q <sub>gs</sub>	Gate Charge Gate to Source	I <sub>D</sub> = 20A		2.4		nC
Q <sub>g(th)</sub>	Gate Charge at Vth			1.3		nC
Q <sub>oss</sub>	Output Charge	V <sub>DS</sub> = 13V, V <sub>GS</sub> = 0V		17		nC
t <sub>d(on)</sub>	Turn On Delay Time			6.1		ns
t <sub>r</sub>	Rise Time	$V_{DS} = 12.5V, V_{GS} = 4.5V,$		10.7		ns
t <sub>d(off)</sub>	Turn Off Delay Time	$I_D = 20A$ , $R_G = 2\Omega$		12.3		ns
t <sub>f</sub>	Fall Time			3.7		ns
Diode Cl	haracteristics	·				
V <sub>SD</sub>	Diode Forward Voltage	I <sub>SD</sub> = 20A, V <sub>GS</sub> = 0V		8.0	1	V
Q <sub>rr</sub>	Reverse Recovery Charge	$V_{DD} = 13V$ , $I_F = 20A$ , $di/dt = 300A/\mu s$		19		nC
t <sub>rr</sub>	Reverse Recovery Time	$V_{DD} = 13V$ , $I_F = 20A$ , $di/dt = 300A/\mu s$		21		ns

## THERMAL CHARACTERISTICS

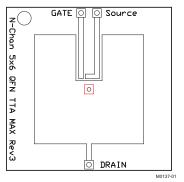
(T<sub>A</sub> = 25°C unless otherwise stated)

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case <sup>(1)</sup>			2.4	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (1) (2)			50	°C/W

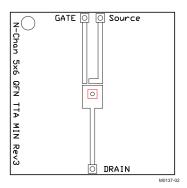
 <sup>(1)</sup> R<sub>θJC</sub> is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. R<sub>θJC</sub> is specified by design, whereas R<sub>θJA</sub> is determined by the user's board design.
 (2) Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.

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Max  $R_{\theta JA} = 50^{\circ} C/W$  when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max  $R_{\theta JA} = 123^{\circ} C/W$  when mounted on minimum pad area of 2-oz. (0.071-mm thick) Cu.

#### TYPICAL MOSFET CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise stated)

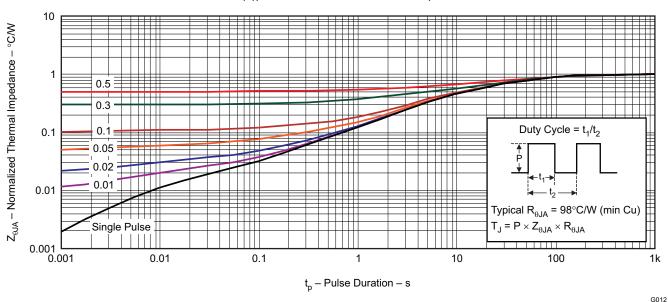


Figure 1. Transient Thermal Impedance

G0 12



## **TYPICAL MOSFET CHARACTERISTICS (continued)**

## $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

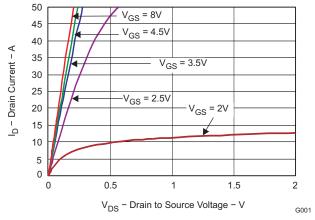


Figure 2. Saturation Characteristics

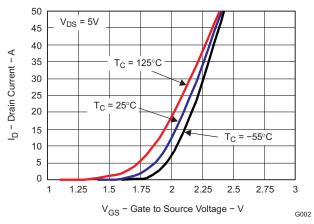


Figure 3. Transfer Characteristics

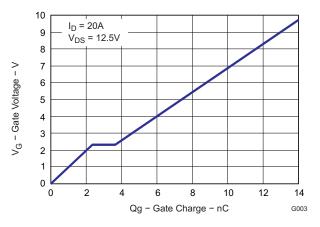


Figure 4. Gate Charge

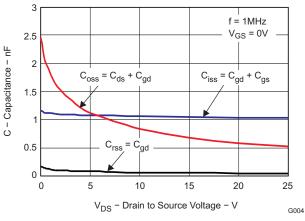


Figure 5. Capacitance

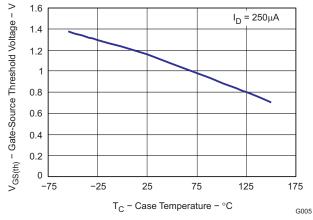


Figure 6. Threshold Voltage vs. Temperature

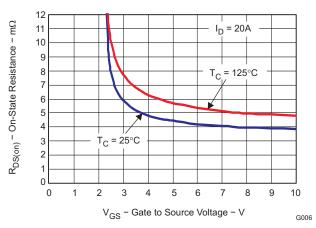


Figure 7. On-State Resistance vs. Gate to Source Voltage



## **TYPICAL MOSFET CHARACTERISTICS (continued)**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

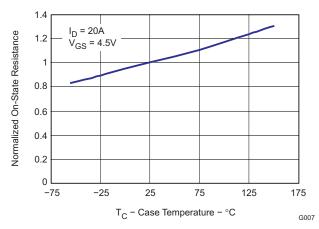


Figure 8. Normalized On-State Resistance vs. Temperature

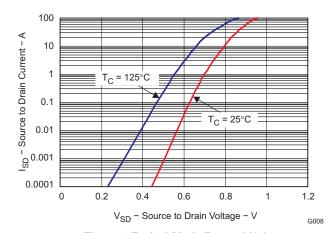


Figure 9. Typical Diode Forward Voltage

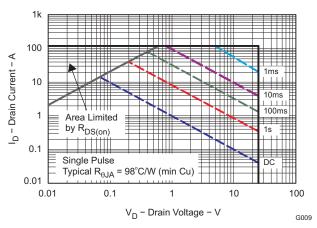


Figure 10. Maximum Safe Operating Area

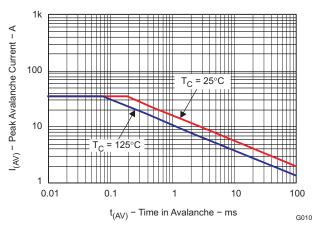


Figure 11. Single Pulse Unclamped Inductive Switching

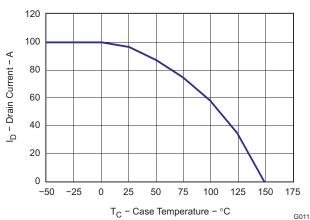
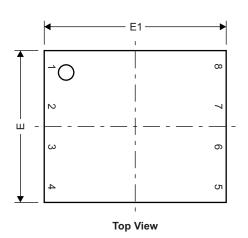


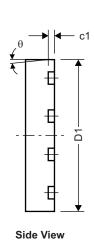
Figure 12. Maximum Drain Current vs. Temperature

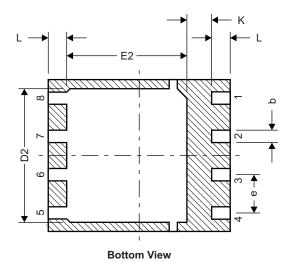


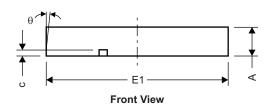
## **MECHANICAL DATA**

## **Q5 Package Dimensions**





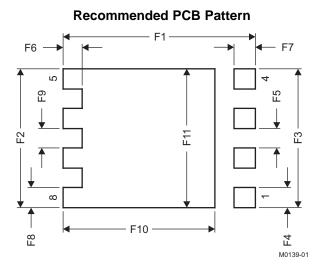




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DIM	MILLIM	ETERS	INCHES			
DIM	MIN	MAX	MIN	MAX		
А	0.950	1.050	0.037	0.039		
b	0.360	0.460	0.014	0.018		
С	0.150	0.250	0.006	0.010		
c1	0.150	0.250	0.006	0.010		
D1	4.900	5.100	0.193	0.201		
D2	4.320	4.520	0.170	0.178		
Е	4.900	5.100	0.193	0.201		
E1	5.900	6.100	0.232	0.240		
E2	3.920	4.12	0.154	0.162		
е	1.27	TYP	0.0	50		
K	0.760	_	0.030	·		
L	0.510	0.710	0.020	0.028		
θ	0.00					

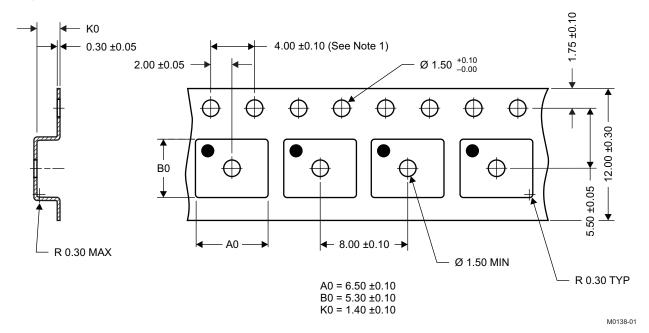




DIM	MILLIN	IETERS	INCHES		
DIN	MIN	MAX	MIN	MAX	
F1	6.205	6.305	0.244	0.248	
F2	4.460	4.560	0.176	0.180	
F3	4.460	4.560	0.176	0.180	
F4	0.650	0.700	0.026	0.028	
F5	0.620	0.670	0.024	0.026	
F6	0.630	0.680	0.025	0.027	
F7	0.700	0.800	0.028	0.031	
F8	0.650	0.700	0.026	0.028	
F9	0.620	0.670	0.024	0.026	
F10	4.900	5.000	0.193	0.197	
F11	4.460	4.560	0.176	0.180	

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

## **Q5 Tape and Reel Information**



#### Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm, unless otherwise specified.
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
- 6. MSL1 260°C (IR and convection) PbF reflow compatible



## **REVISION HISTORY**

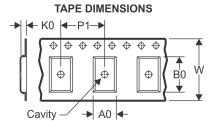
Cha	anges from Original (August 2009) to Revision A	Page
• (	Changed Note1 of the ABSOLUTE MAXIMUM RATINGS From: $R_{\theta JA} = 39^{\circ}$ C/W To: Typical $R_{\theta JA} = 39^{\circ}$ C/W	1
• (	Changed Figure 1 text From: R <sub>eJA</sub> = 99°C/W To: Typical R <sub>eJA</sub> = 98°C/W	3
• (	Changed Figure 10 text From: R <sub>eJA</sub> = 99°C/W To: Typical R <sub>eJA</sub> = 98°C/W	5
• (	Changed Figure 11 X- axis values	5
Cha	anges from Revision A (April 2010) to Revision B	Page
• (	Changed $R_{DS(on)}$ - $V_{GS}$ = 3V in the Electrical Characteristics table From: 7 To: 7.2 in the max column	2
•	Deleted the Package Marking Information section	7

## PACKAGE MATERIALS INFORMATION

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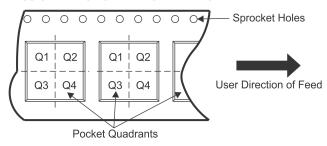
## TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

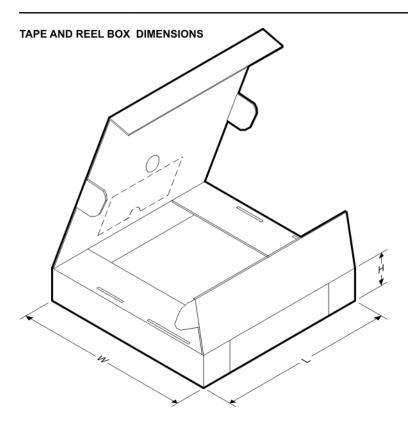
## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16322Q5	VSON- CLIP	DQH	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1

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#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD16322Q5	VSON-CLIP	DQH	8	2500	335.0	335.0	32.0

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